SGF40N60UFD

CO-PAK IGBT

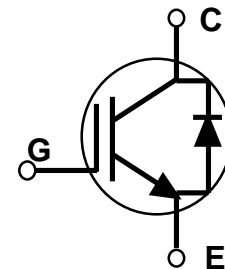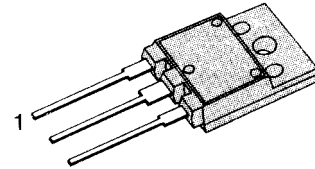## FEATURES

* High Speed Switching
* Low Saturation Voltage
     : V_{CE}(sat) = 2.0 V (@ Ic=20A)
* High Input Impedance
*CO-PAK, IGBT with FRD
     : Trr = 42nS (typ.)

APPLICATIONS

* AC & DC Motor controls
* General Purpose Inverters
* Robotics , Servo Controls
* Power Supply
* Lamp Ballast

TO-3PF

ABSOLUTE   MAXIMUM RATINGS

Symbol	Characteristics	Rating	Units
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate-Emitter Voltage	±20	V
I_C	Collector Current @ Tc = 25°C	40	A
	Collector Current @ Tc = 100°C	20	A
$I_{CM\,(1)}$	Pulsed Collector Current	160	A
I_F	Diode Continuous Forward Current @ Tc = 100°C	15	A
I_{FM}	Diode Maximum Forward Current	160	A
P_D	Maximum Power Dissipation @Tc = 25°C	96	W
	Maximum Power Dissipation @Tc = 100°C	38	W
Tj	Operating Junction Temperature	-55 ~ 150	°C
Tstg	Storage Temperature Range	-55 ~ 150	°C
TL	Maximum Lead Temp. For Soldering Purposes, 1/8" from case for 5 seconds	300	°C

Notes:(1) Repetitive rating : Pulse width limited by max. junction temperature

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Rev.B

ELECTRICAL CHARACTERISTICS (IGBT PART)
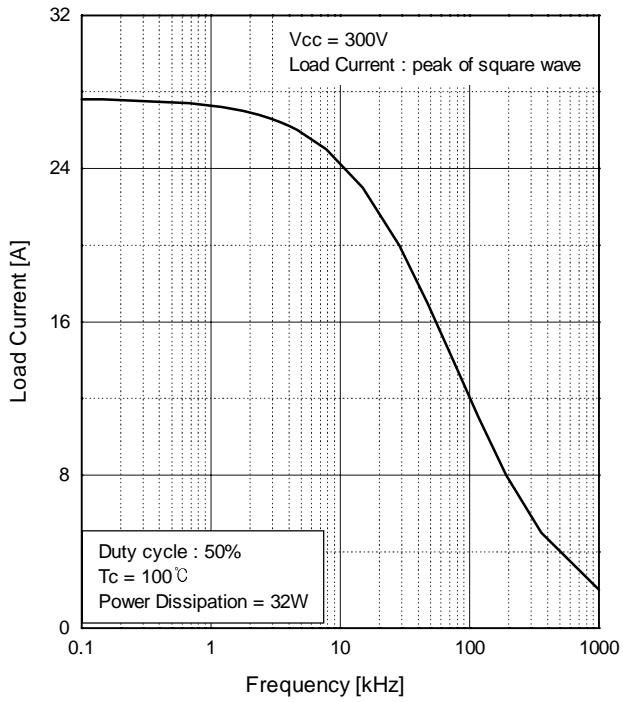**(T_C=25°C,Unless Otherwise Specified)**

Symbol	Characteristics	Test Conditions	Min	Typ	Max	Units
BV_{CES}	C - E Breakdown Voltage	V_{GE} = 0V , I_C = 250uA	600	-	-	V
$\Delta V_{CES/}$ ΔT_J	Temperature Coeff. of Breakdown Voltage	V_{GE} = 0V , I_C = 1mA	-	0.6	-	V/°C
$V_{GE(th)}$	G - E threshold voltage	I_C = 20mA , V_{CE} = V_{GE}	4.5	5.5	7.5	V
I_{CES}	Collector cutoff Current	V_{CE} = V_{CES} , V_{GE} = 0V	-	-	250	uA
I_{GES}	G - E leakage Current	V_{GE} = V_{GES} , V_{CE} = 0V	-	-	100	nA
V_{CE}(sat)	Collector to Emitter saturation voltage	Ic=20A, V_{GE} = 15V	-	2.0	2.6	V
		Ic=40A, V_{GE} = 15V	-	2.6	-	V
Cies	Input capacitance	V_{GE} = 0V , f = 1MHz	-	1430	-	pF
Coes	Output capacitance	V_{CE} = 30V	-	168	-	pF
Cres	Reverse transfer capacitance		-	50	-	pF
td(on)	Turn on delay time	V_{CC} = 300V , I_C = 20A	-	12	-	ns
tr	Turn on rise time	V_{GE} = 15V	-	20	-	ns
td(off)	Turn off delay time	R_G = 10Ω	-	68	100	ns
tf	Turn off fall time	Inductive Load	-	50	100	ns
Eon	Turn on Switching Loss		-	0.08	-	mJ
Eoff	Turn off Switching Loss		-	0.19	-	mJ
Ets	Total Switching Loss		-	0.27	0.47	mJ
Qg	Total Gate Charge	Vcc = 300V	-	92	138	nC
Qge	Gate-Emitter Charge	V_{GE} = 15V	-	21	31	nC
Qgc	Gate-Collector Charge	Ic = 20A	-	28	42	nC
Le	Internal Emitter Inductance	Measured 5mm from PKG	-	14	-	nH

ELECTRICAL CHARACTERISTICS (DIODE PART)
(T_C=25°C,Unless Otherwise Specified)

Symbol	Characteristics	Test Conditions		Min	Typ	Max	Units
V_{FM}	Diode Forward Voltage	I_F=15A	Tc =25°C	-	1.4	1.7	V
			Tc =100°C	-	1.3	-	
Trr	Diode Reverse Recovery Time	I_F=15A, V_R=200V -di/dt=200A/uS	Tc =25°C	-	42	60	nS
			Tc =10 °C	-	74	-	
Irr	Diode Peak Reverse Recovery Current		Tc =25°C	-	4.0	6.0	A
			Tc =10 °C	-	6.5	-	
Qrr	Diode Reverse Recovery Charge		Tc =25°C	-	80	180	nC
			Tc =100°C	-	220	-	

THERMAL RESISTANCE

Symbol	Characteristics	Min	Typ	Max	Units
$R_{\theta}JC$	Junction-to-Case (IGBT)	-	-	1.3	°C/W
$R_{\theta}JC$	Junction-to-Case (DIODE)	-	-	2.5	°C/W
$R_{\theta}JA$	Junction-to-Ambient	-	-	45	°C/W

Fig.1 Typical Load Current vs. Frequency

Fig.2 Typical Output Characteristics

Fig.3 Maximum Collector Current vs.
       Case Temperature

Fig.4 Collector to Emitter Voltage vs.
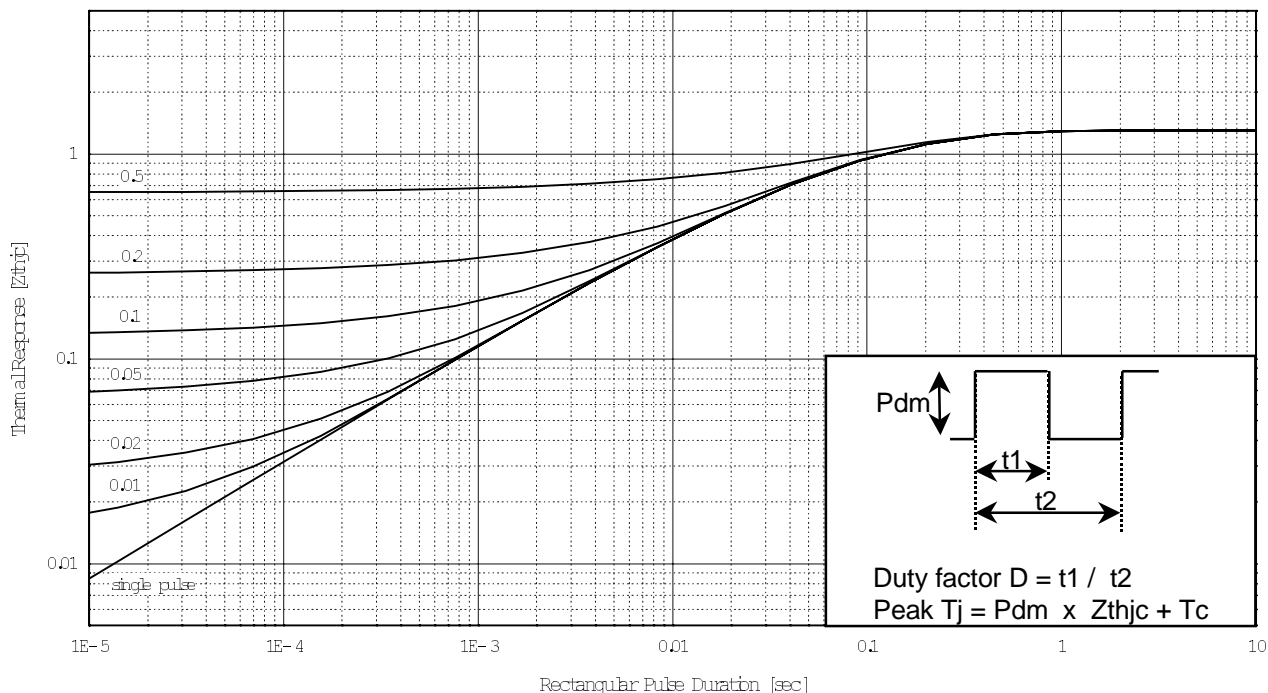   Case Temperature
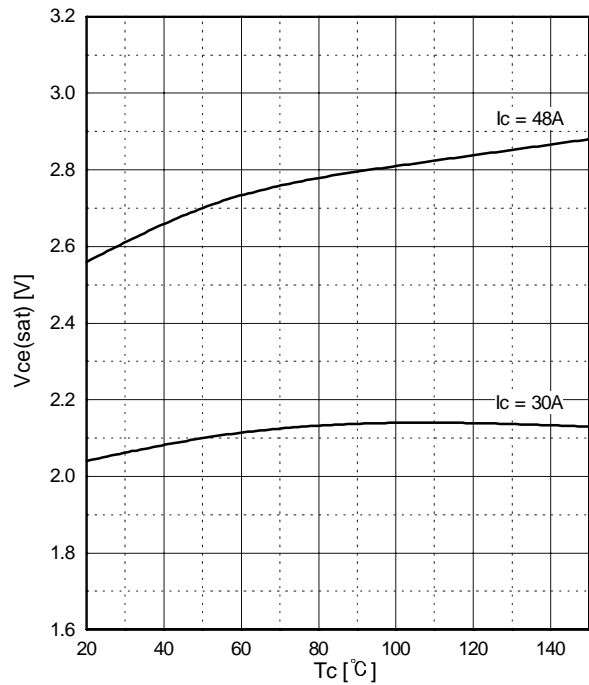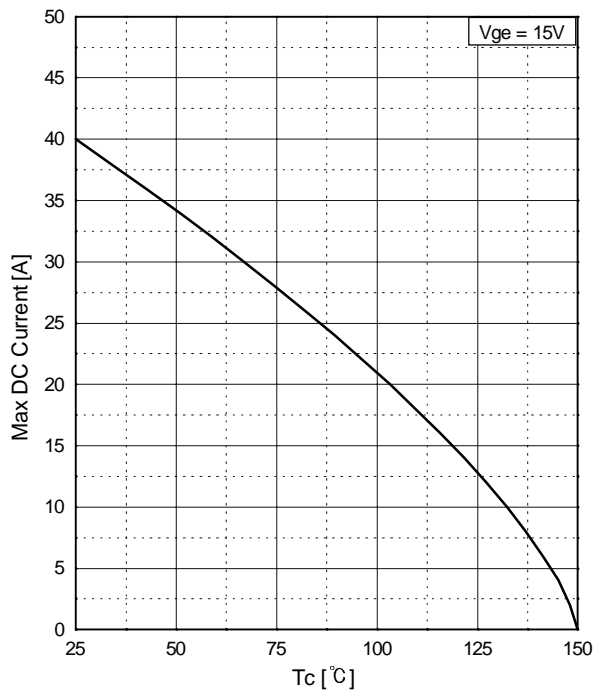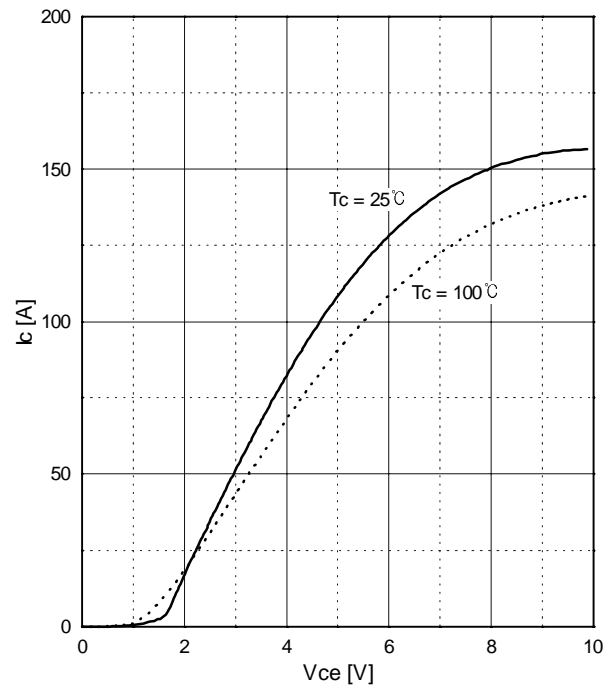
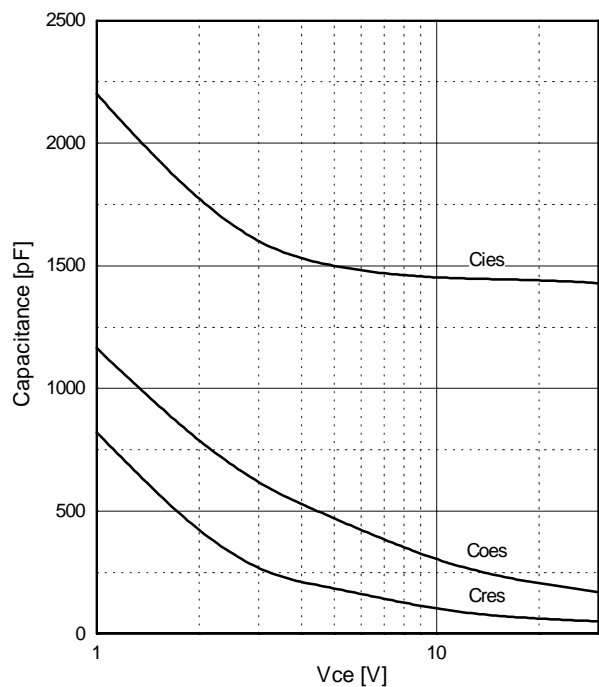Fig.5 Maximum Effective Transient Thermal Impedance, Junction to Case

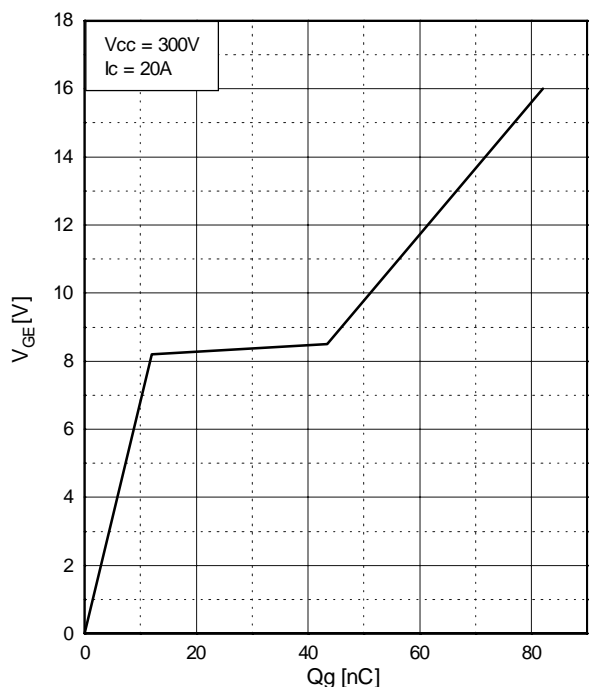Fig.6 Typical Capacitance vs.
     Collector to Emitter Voltage

Fig.7 Typical Gate Charge vs.
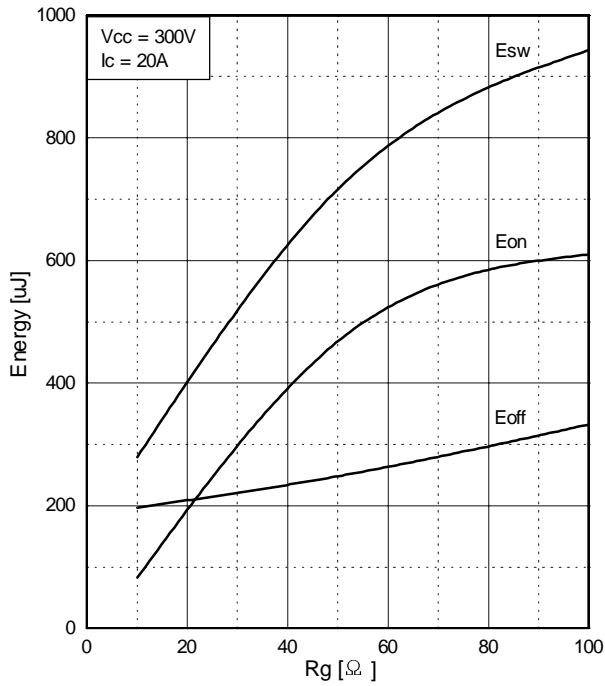   Gate to Emitter Voltage

Fig.8 Typical Switching Loss vs.
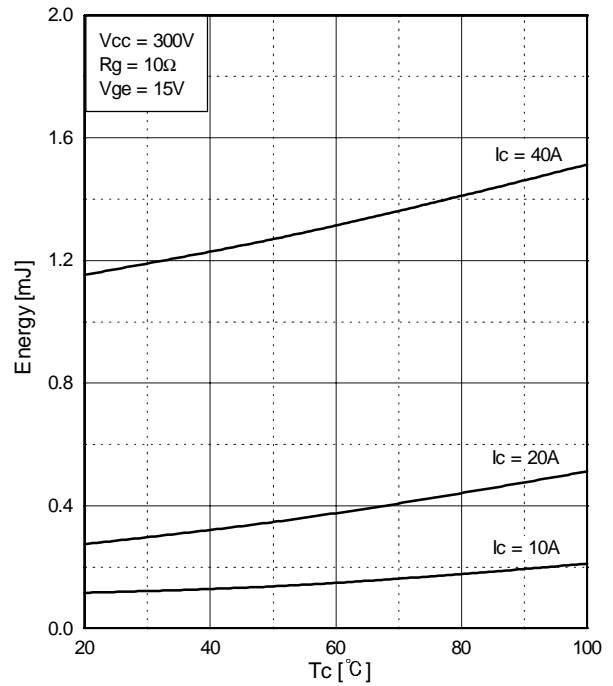Gate Resistance

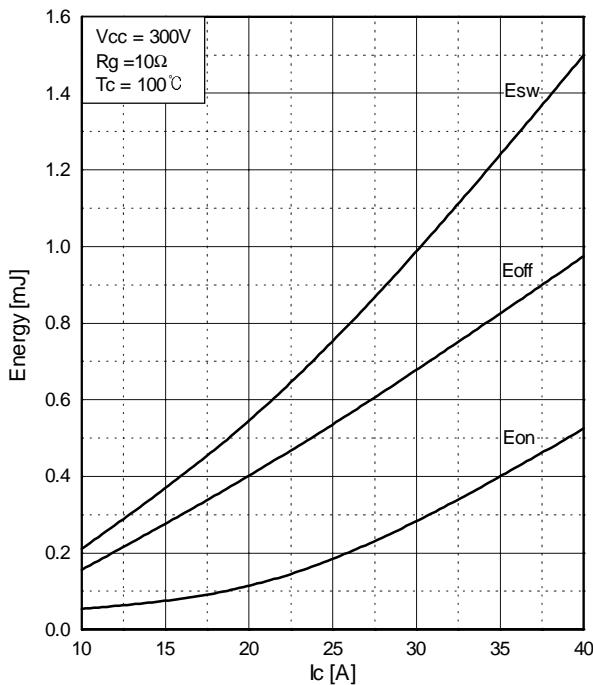Fig.9 Typical Switching Loss vs.
Case Temperature

Fig.10 Typical Switching loss vs.
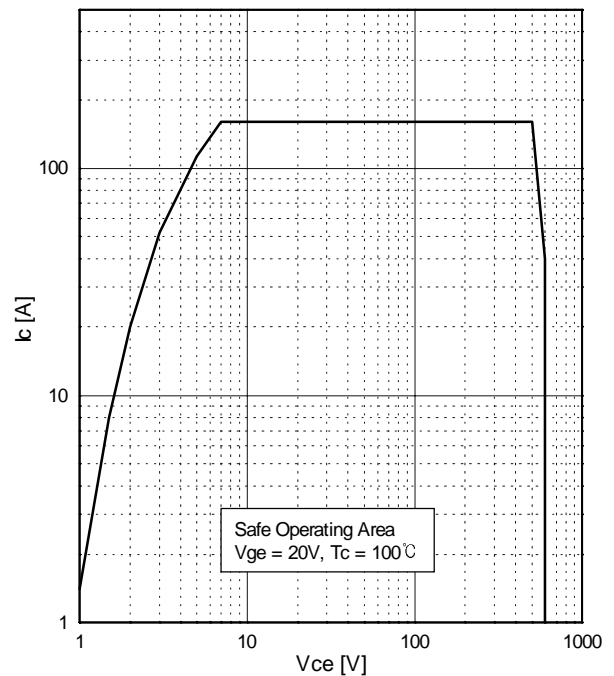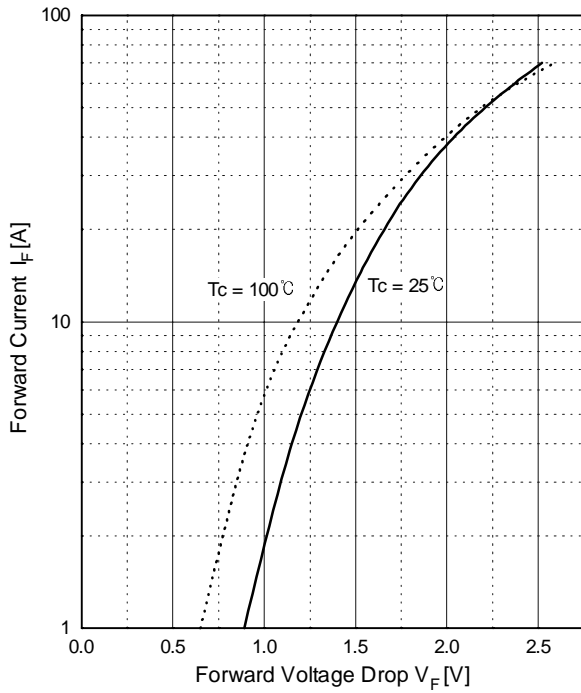Collector to Emitter Current

Fig.11 Turn-off SOA

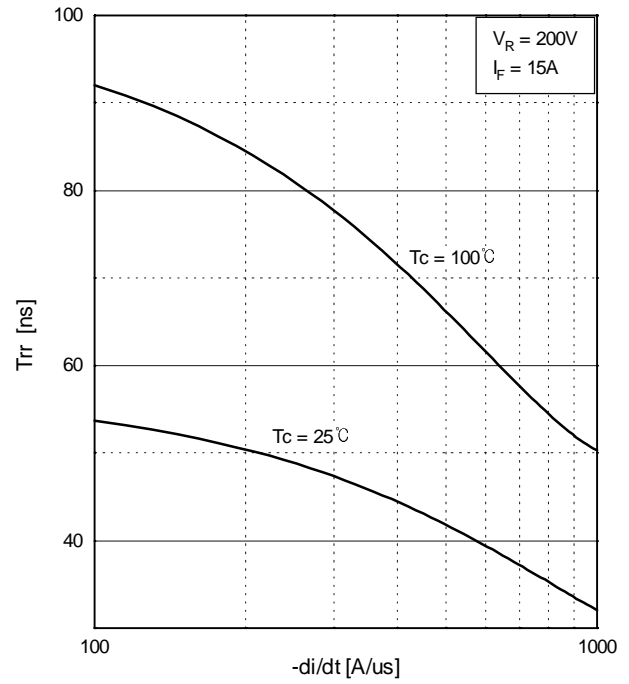Fig.12 Typical Forward Voltage Drop
vs. Forward Current

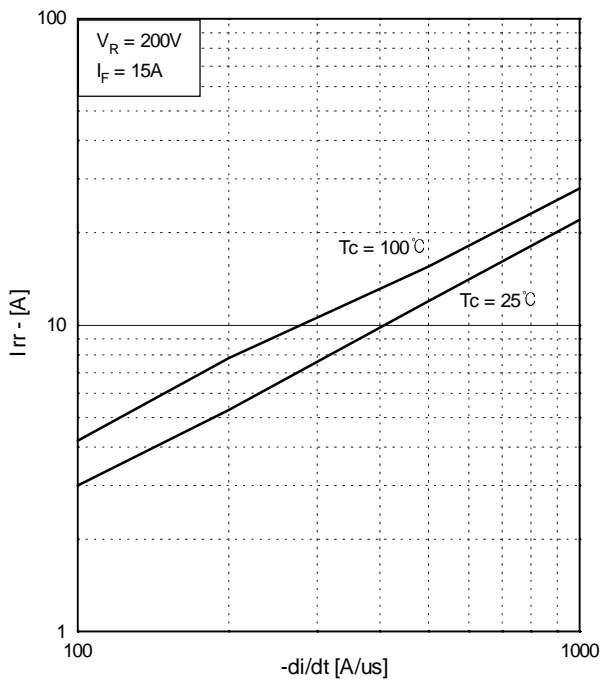Fig.13 Typical Reverse Recovery Time
vs. di/dt
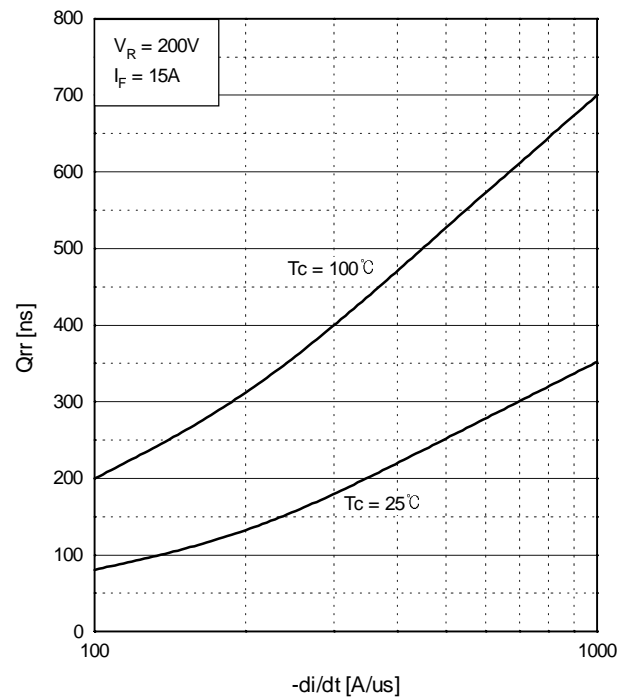

Fig.14 Typical Reverse Recovery Current
vs. di/dt

Fig.15 Typical Stored Charge vs. di/dt

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